

MS75N75

75V N-Channel MOSFET

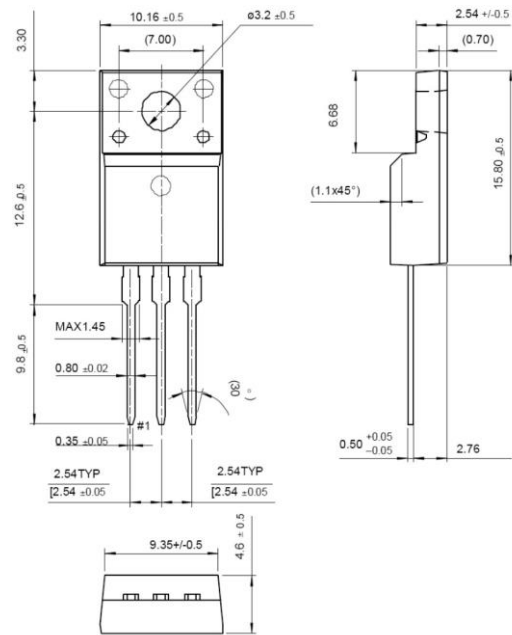
Features

- RDS(on) (Max 0.017 Ω)@VGS=10V
- Gate Charge (Typical 85nC)
- Improved dv/dt Capability, High Ruggedness
- 100% Avalanche Tested
- Maximum Junction Temperature Range (175°C)
- RoHS compliant package

Package type : TO-220AB

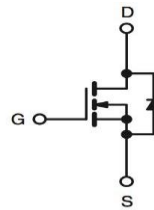
Packing & Order Information

50/Tube ; 1,000/Box



**RoHS
COMPLIANT**

Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	75	V
I _D	Drain Current -Continuous (TC=25°C)	75	A
	Drain Current -Continuous (TC=100°C)	52.5	A
I _{DM}	Drain Current -Pulsed	300	A
V _{GS}	Gate-Source Voltage	±20	V
E _{AS}	Single Pulsed Avalanche Energy	1350	mJ
E _{AR}	Repetitive Avalanche Energy	9	mJ
dv/dt	Peak Diode Recovery dv/dt	7.0	V/ns
P _D	Power Dissipation (TC=25°C) - Derate above 25°C	190	W
		1.27	W/°C
T _J /T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

● Drain current limited by maximum junction temperature

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Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.43	°C/W
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = 10 V, I_D = 3.75 A$	--	14	17	mΩ

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250\mu A$	75	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25°C	--	0.08	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 75 V, V_{GS} = 0 V$ $V_{DS} = 60 V, V_C = 125^\circ C$	--	--	10 100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 V, V_{DS} = 0 V$	--	--	100	μA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 V, V_{DS} = 0 V$	--	--	-100	nA

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
C_{ISS}	Input Capacitance	$V_{DS} = 25 V, V_{GS} = 0 V,$ $f = 1.0 MHz$	--	3000	--	pF
C_{OSS}	Coss Output Capacitance		--	1100	--	pF
C_{RSS}	Crss Reverse Transfer Capacitance		--	250	--	pF

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Time	$V_{DS} = 37.5 V, I_D = 75 A,$ $R_G = 25 \Omega$	--	25	60	ns
t_r	Turn-On Rise Time		--	300	700	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	310	ns
t_f	Turn-Off Fall Time		--	180	370	ns
Q_g	Total Gate Charge	$V_{DS} = 60 V, I_D = 10 A,$ $V_{GS} = 75 V$	--	85	110	nC
Q_{gs}	Gate-Source Charge		--	15	--	nC
Q_{gd}	Gate-Drain Charge		--	40	--	nC

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Source-Drain Diode Maximum Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
I_S	Continuous Source-Drain Diode Forward Current		--	--	75	A
I_{SM}	ISM Pulsed Source-Drain Diode Forward Current		--	--	300	
V_{SD}	Source-Drain Diode Forward Voltage	$I_S = 75\text{ A}, V_{GS} = 0\text{ V}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S = 75\text{ A}, V_{GS} = 0\text{ V}$ $diF/dt = 100\text{ A}/\mu\text{s}$	--	90	--	ns
Q_{rr}	Reverse Recovery Charge		--	250	--	μC

Notes :

1. Repeativity rating : pulse width limited by junction temperature
2. $L = 0.32\text{mH}$, $I_{AS} = 75\text{A}$, $V_{DD} = 25\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 75\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq \text{BVDSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially independent of operating temperature.

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